## MBD110DWT1G, MBD330DWT1G

## Dual Schottky Barrier Diodes

Application circuit designs are moving toward the consolidation of device count and into smaller packages. The new SOT-363 package is a solution which simplifies circuit design, reduces device count, and reduces board space by putting two discrete devices in one small six-leaded package. The SOT-363 is ideal for low-power surface mount applications where board space is at a premium, such as portable products.

## Surface Mount Comparisons:

|  | SOT-363 | SOT-23 |
| :--- | :---: | :---: |
| Area $\left(\mathrm{mm}^{2}\right)$ | 4.6 | 7.6 |
| Max Package $\mathrm{P}_{\mathrm{D}}(\mathrm{mW})$ | 120 | 225 |
| Device Count | 2 | 1 |

## Space Savings:

| Package | $\mathbf{1} \times$ SOT-23 | $\mathbf{2} \times$ SOT-23 |
| :---: | :---: | :---: |
| SOT-363 | $40 \%$ | $70 \%$ |

The MBD110DW and MBD330DW devices are spin-offs of our popular MMBD101LT1 and MMBD301LT1 SOT-23 devices. They are designed for high-efficiency UHF and VHF detector applications. Readily available to many other fast switching RF and digital applications.

## Features

- Extremely Low Minority Carrier Lifetime
- Very Low Capacitance
- Low Reverse Leakage
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant


## MAXIMUM RATINGS

| Rating |  | Symbol | Value | Unit |
| :--- | ---: | :---: | :---: | :---: |
| Reverse VoltageMBD110DWT1G <br> MBD330DWT1G | $\mathrm{V}_{\mathrm{R}}$ | 7.0 <br> 30 | V |  |
| Forward Current (DC) | MBD330DWT1G | $\mathrm{I}_{\mathrm{F}}$ | 200 Max | mA |
| Forward Power Dissipation $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ | $\mathrm{P}_{\mathrm{F}}$ | 120 | mW |  |
| Junction Temperature | $\mathrm{T}_{\mathrm{J}}$ | -55 to +125 | ${ }^{\circ} \mathrm{C}$ |  |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |  |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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## MARKING DIAGRAM


xx = Device Code Refer to Ordering Table, page 2
M = Date Code

- = Pb-Free Package
(Note: Microdot may be in either location)


## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Reverse Breakdown Voltage $\left(I_{R}=10 \mu \mathrm{~A}\right)$ | MBD110DWT1G MBD330DWT1G | $\mathrm{V}_{(\mathrm{BR}) \mathrm{R}}$ | $\begin{aligned} & 7.0 \\ & 30 \end{aligned}$ | 10 | - | V |
| Diode Capacitance $\left(\mathrm{V}_{\mathrm{R}}=0, \mathrm{f}=1.0 \mathrm{MHz}\right. \text {, Note 1) }$ | MBD110DWT1G | $\mathrm{C}_{\mathrm{D}}$ | - | 0.88 | 1.0 | pF |
| Total Capacitance $\left(\mathrm{V}_{\mathrm{R}}=15\right.$ Volts, $\left.\mathrm{f}=1.0 \mathrm{MHz}\right)$ | MBD330DWT1G | $\mathrm{C}_{\text {T }}$ | - | 0.9 | 1.5 | pF |
| Reverse Leakage $\begin{aligned} & \left(V_{R}=3.0 \mathrm{~V}\right) \\ & \left(\mathrm{V}_{\mathrm{R}}=25 \mathrm{~V}\right) \end{aligned}$ | MBD110DWT1G MBD330DWT1G | $\mathrm{I}_{\mathrm{R}}$ | - | $\begin{gathered} 0.02 \\ 13 \end{gathered}$ | $\begin{aligned} & 0.25 \\ & 200 \end{aligned}$ | $\begin{aligned} & \mu \mathrm{A} \\ & \mathrm{nA} \end{aligned}$ |
| Noise Figure $(f=1.0 \mathrm{GHz} \text {, Note 2) }$ | MBD110DWT1G | NF | - | 6.0 | - | dB |
| Forward Voltage $\begin{aligned} & \left(I_{F}=10 \mathrm{~mA}\right) \\ & \left(\mathrm{I}_{\mathrm{F}}=1.0 \mathrm{~mA}\right) \\ & \left(\mathrm{I}_{F}=10 \mathrm{~mA}\right) \end{aligned}$ | MBD110DWT1G MBD330DWT1G | $\mathrm{V}_{\mathrm{F}}$ | - | $\begin{gathered} 0.5 \\ 0.38 \\ 0.52 \end{gathered}$ | $\begin{gathered} 0.6 \\ 0.45 \\ 0.6 \end{gathered}$ | V |

## ORDERING INFORMATION

| Device | Marking | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: | :---: |
| MBD110DWT1G | M4 | SC-88 / SOT-363 <br> (Pb-Free) | 3000 Units / Tape \& Reel |
| MBD330DWT1G | T4 |  |  |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MBD110DWT1G, MBD330DWT1G

## TYPICAL CHARACTERISTICS MBD110DWT1G



Figure 1. Reverse Leakage


Figure 3. Capacitance


Figure 2. Forward Voltage


## NOTES ON TESTING AND SPECIFICATIONS

Note $1-C_{D}$ and $C_{T}$ are measured using a capacitance bridge (Boonton Electronics Model 75A or equivalent).
Note 2 - Noise figure measured with diode under test in tuned diode mount using UHF noise source and local oscillator (LO) frequency of 1.0 GHz . The LO power is adjusted for 1.0 mW . IF amplifier $\mathrm{NF}=1.5 \mathrm{~dB}, \mathrm{f}=30 \mathrm{MHz}$, see Figure 5.
Note 3 - $L_{S}$ is measured on a package having a short instead of a die, using an impedance bridge (Boonton Radio Model 250A RX Meter).

Figure 5. Noise Figure Test Circuit

## MBD110DWT1G, MBD330DWT1G

TYPICAL CHARACTERISTICS MBD330DWT1G


Figure 6. Total Capacitance


Figure 8. Reverse Leakage


Figure 7. Minority Carrier Lifetime


Figure 9. Forward Voltage


RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 2. CONTROLLING DIMENSION: MILLIMETERS.
2. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
3. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DIMENSIONS D AND E1 AT THE OUT
THE PLASTIC BODY AND DATUM H.
THE PLASTIC BODY AND DATUM H.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE DIMENSIONS b AND c APPLY TO THE FLAT SEC
LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
6. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | -- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC |  |  | 0.006 BSC |  |  |
| aaa | 0.15 |  |  | 0.006 |  |  |
| bbb | 0.30 |  |  | 0.012 |  |  |
| ccc | 0.10 |  |  | 0.004 |  |  |
| ddd | 0.10 |  |  | 0.004 |  |  |
|  | GENERIC |  |  |  |  |  |
|  | MARKING DIAGRAM* |  |  |  |  |  |



XXX $=$ Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.


## STYLES ON PAGE 2

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## SC-88/SC70-6/SOT-363

CASE 419B-02
ISSUE Y
STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 19:
PIN 1. IOUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF
STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1
STYLE 2:

CANCELLED
STYLE 8:
CANCELLED

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR
STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAAN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

| STYLE 3 : CANCELLED | STYLE 4: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. ANODE | STYLE 5: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. CATHODE | STYLE 6 : <br> PIN 1. ANODE 2 <br> 2. $\mathrm{N} / \mathrm{C}$ <br> 3. CATHODE 1 <br> 4. ANODE 1 <br> 5. N/C <br> 6. CATHODE 2 |
| :---: | :---: | :---: | :---: |
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: |
| PIN 1. EMITTER 2 | PIN 1. SOURCE 2 | PIN 1. CATHODE 2 | PIN 1. ANODE 2 |
| 2. EMITTER 1 | 2. SOURCE 1 | 2. CATHODE 2 | 2. ANODE 2 |
| 3. COLLECTOR 1 | 3. GATE 1 | 3. ANODE 1 | 3. CATHODE 1 |
| 4. BASE 1 | 4. DRAIN 1 | 4. CATHODE 1 | 4. ANODE 1 |
| 5. BASE 2 | 5. DRAIN 2 | 5. CATHODE 1 | 5. ANODE 1 |
| 6. COLLECTOR 2 | 6. GATE 2 | 6. ANODE 2 | 6. CATHODE 2 |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. $\mathrm{N} / \mathrm{C}$ | 2. GND | 2. CH 1 | 2. ANODE |
| 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. N/C | 5. VBUS | 5. CH 2 | 5. CATHODE |
| 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 27: | STYLE 28 : | STYLE 29: | STYLE 30: |
| PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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